EGN21C030MK

High Voltage - High Power GaN-HEMT

FEATURES

・High Voltage Operation : VDS=50V
・High Power : 45.0dBm (typ.) @ Psat
・Power Gain : 19dB (typ.) @ f=2.14GHz
・Proven Reliability

DESCRIPTION

SEI's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power L-band amplifiers with 50V operation, and gives you higher gain.
This new product is ideally suited for use in 2.1GHz W-CDMA and LTE design requirements as it offers high gain, long term reliability and ease of use.

ABSOLUTE MAXIMUM RATINGS (Case Temperature Tc=25deg.C)

Item	Symbol	Condition	Rating	Unit
Operating Voltage	VDS		55	V
Drain-Source Voltage	VDS	VGS=-8V	160	V
Gate-Source Voltage	VGS		-15	V
Total Power Dissipation	Pt		37.5	W
Storage Temperature	Tstg		-65 to +175	deg.C
Channel Temperature	Tch		250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	VDS		≤ 55	V
Forward Gate Current	IGF	RG=15ohm	≤ 69	mA
Reverse Gate Current	IGR	RG=15ohm	≥ -1.1	mA
Channel Temperature	Tch		≤ 180	deg.C
Average Output Power	Pave.		≤ 42.0	dBm

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25deg.C)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	Vp	VDS=50V, IDS=7.8mA	-1.0	-1.5	-2.0	V
Saturated Power	Psat *1	VDS=50V	44.0	45.0	-	dBm
Drain Efficiency	ηd *2	IDS(DC)=150mA	10.5	12.5	-	%
Power Gain	Gp *2	f=2.14GHz	18.0	19.0	-	dB
Thermal Resistance	Rth	Channel to Case at 24W PDC	-	5.0	6.0	deg.C/W

*1 : 10%-duty RF pulse (DC supply constant)
*2 : Pout=31.5dBm, CW

RoHS COMPLIANCE	Yes

SUMITOMO ELECTRIC

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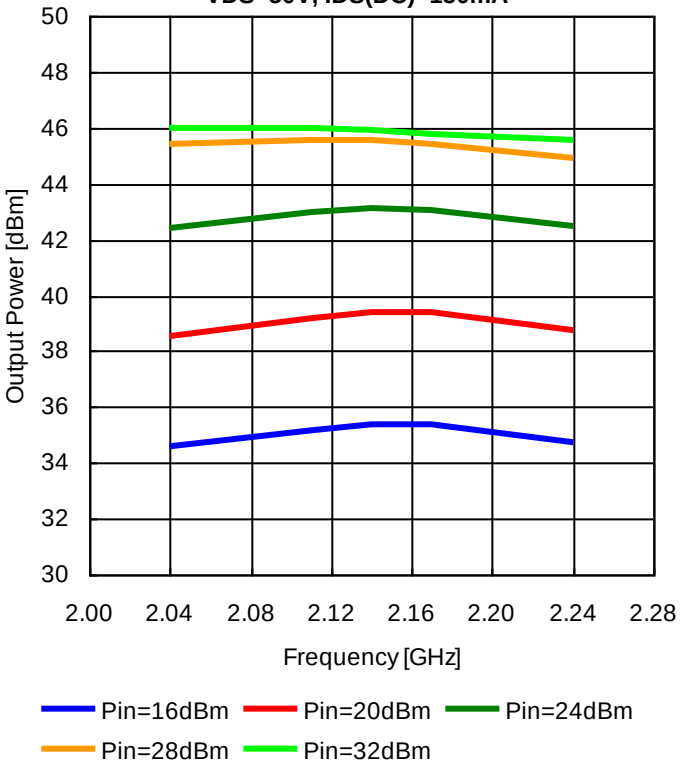
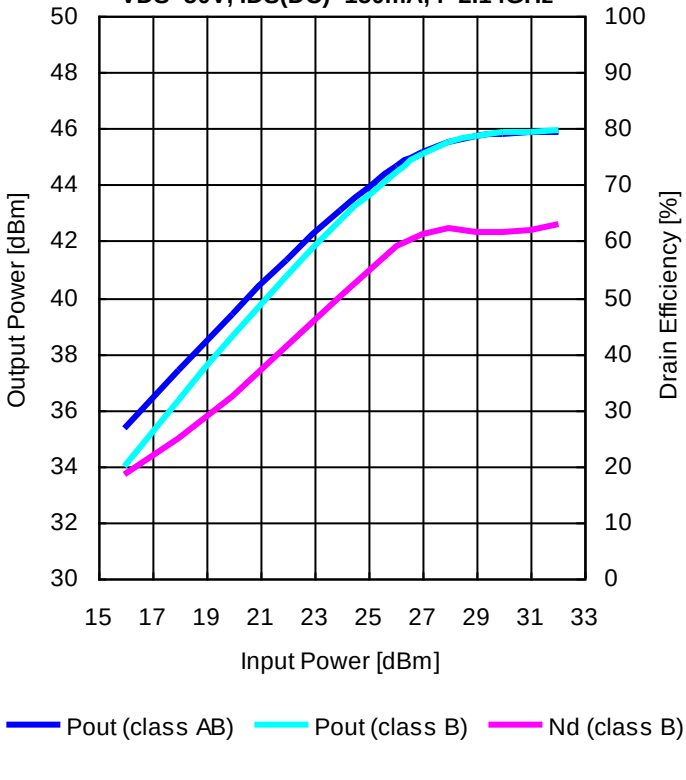
RF characteristics @f=2.14GHz fine tuned

Output Power vs. Frequency
VDS=50V, IDS(DC)=150mA

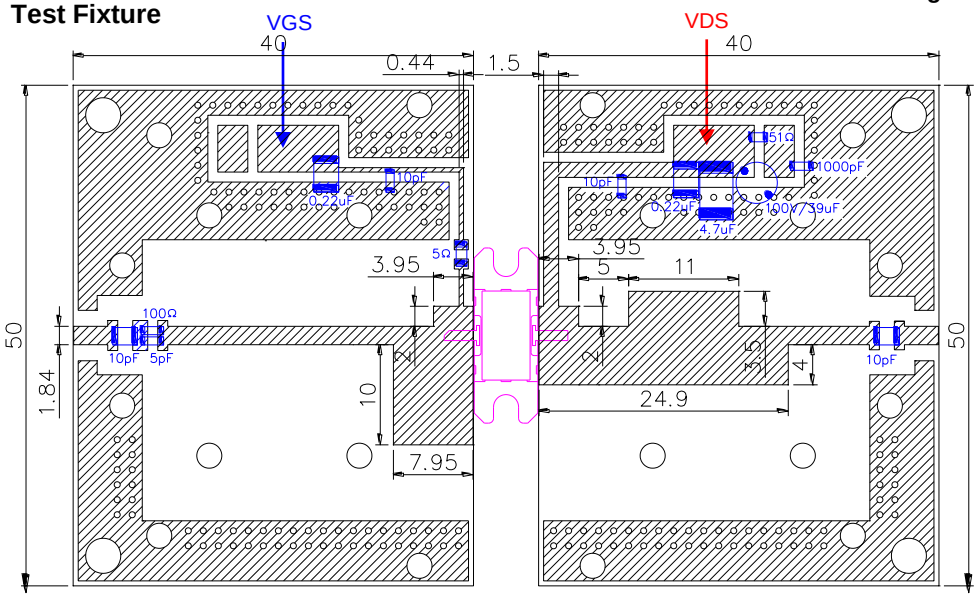


Output Power and Drain Efficiency vs. Input Power
VDS=50V, IDS(DC)=150mA, f=2.14GHz



Pulse Signal (10%-duty, DC : constant)

Test Fixture



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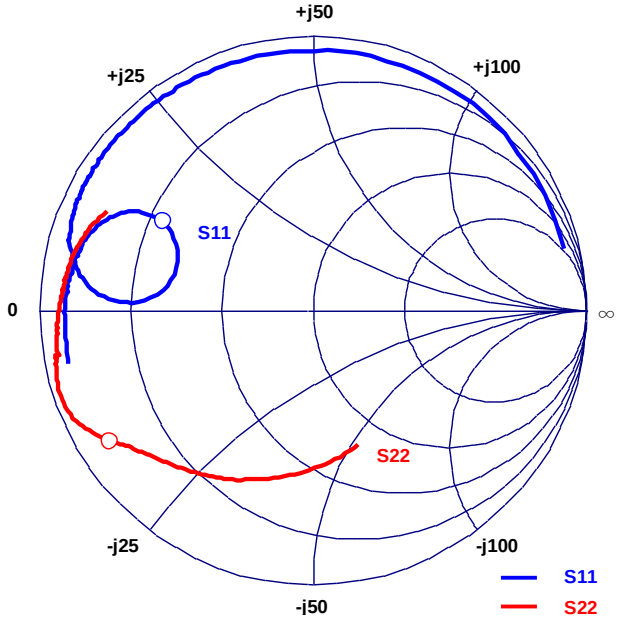
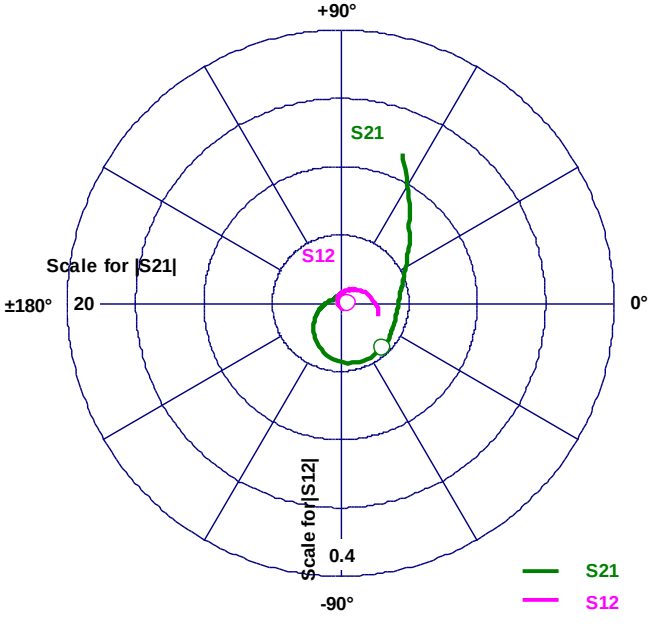
- Reference DATA -

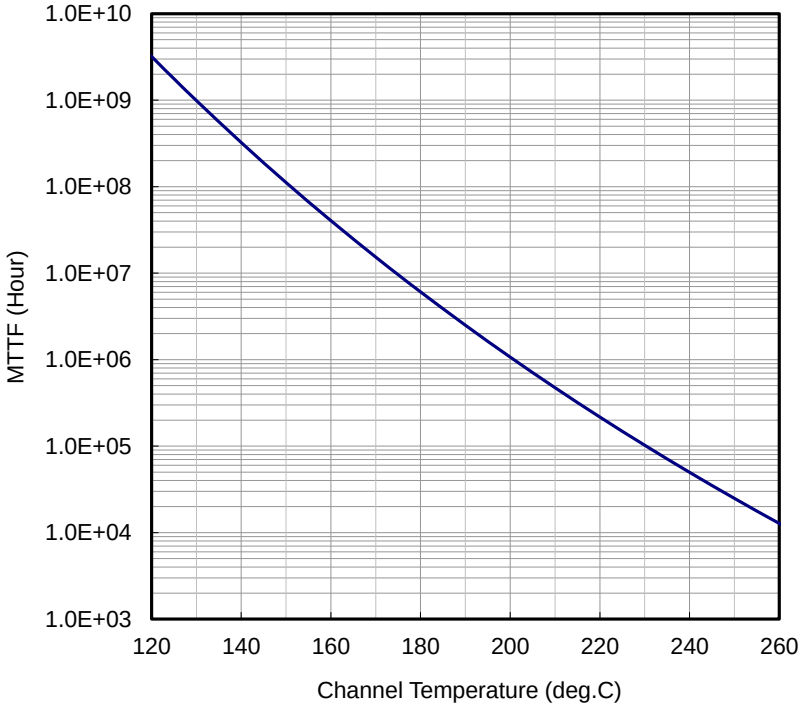
S-Parameters @VDS=50V, IDS(DC)=150mA, f=0.5 to 5.5GHz
Zl = Zs = 50ohm Marker : 2.14GHz





Freq.	S11		S21		S12		S22	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.50	0.92	-167.76	11.88	67.33	0.007	-1.05	0.52	-71.31
0.60	0.91	-172.44	9.91	60.12	0.008	-9.94	0.55	-79.39
0.70	0.91	-176.35	8.50	53.22	0.007	-8.07	0.57	-87.12
0.80	0.91	-179.64	7.40	46.87	0.007	-10.93	0.60	-94.46
0.90	0.90	177.22	6.61	39.83	0.007	-8.43	0.62	-101.38
1.00	0.90	174.37	5.93	34.28	0.007	-5.18	0.65	-107.51
1.10	0.90	172.14	5.46	28.05	0.006	-8.73	0.68	-112.74
1.20	0.89	169.65	5.09	22.56	0.006	-11.64	0.70	-117.63
1.30	0.88	167.20	4.78	16.88	0.005	-8.15	0.71	-122.04
1.40	0.88	164.80	4.53	10.93	0.006	3.38	0.73	-126.03
1.50	0.87	162.30	4.38	4.93	0.007	7.18	0.75	-129.81
1.60	0.85	160.12	4.27	-1.03	0.007	-0.84	0.77	-133.16
1.70	0.84	157.53	4.21	-7.87	0.007	7.36	0.79	-136.27
1.80	0.81	155.22	4.21	-14.31	0.008	2.46	0.80	-139.10
1.90	0.78	152.62	4.27	-22.78	0.008	5.59	0.82	-141.54
2.00	0.73	150.55	4.35	-31.36	0.008	-2.59	0.84	-144.10
2.10	0.67	149.70	4.49	-41.55	0.010	-6.62	0.86	-145.87
2.20	0.60	150.44	4.58	-53.44	0.011	-17.62	0.90	-148.41
2.30	0.54	156.11	4.58	-68.01	0.011	-26.30	0.92	-151.11
2.40	0.52	165.55	4.47	-82.96	0.011	-34.31	0.95	-153.98
2.50	0.57	174.45	4.09	-100.02	0.012	-53.88	0.97	-157.62
2.60	0.66	177.90	3.58	-115.25	0.009	-67.79	0.97	-161.15
2.70	0.75	177.13	3.04	-128.27	0.008	-87.49	0.97	-164.01
2.80	0.81	174.57	2.53	-138.81	0.006	-89.61	0.96	-166.41
2.90	0.86	171.89	2.14	-148.70	0.005	-103.89	0.96	-168.36
3.00	0.89	168.51	1.79	-155.37	0.004	-137.30	0.95	-170.12
3.10	0.91	166.09	1.53	-162.57	0.003	-132.30	0.95	-171.70
3.20	0.93	163.76	1.32	-167.51	0.002	171.39	0.94	-173.24
3.30	0.94	160.96	1.15	-172.75	0.003	-179.32	0.94	-174.55
3.40	0.94	158.76	1.01	-177.44	0.003	139.32	0.94	-175.89
3.50	0.95	156.39	0.90	178.06	0.003	132.52	0.93	-177.18
3.60	0.95	154.54	0.81	175.02	0.005	127.36	0.93	-178.48
3.70	0.95	152.38	0.73	170.36	0.005	122.70	0.93	-179.59
3.80	0.95	150.32	0.68	167.48	0.006	112.99	0.93	179.18
3.90	0.95	147.92	0.63	163.44	0.007	102.76	0.92	177.96
4.00	0.95	145.49	0.58	160.11	0.009	106.05	0.92	176.76
4.10	0.95	143.02	0.56	156.87	0.010	95.65	0.92	175.67
4.20	0.95	140.18	0.52	152.60	0.011	87.44	0.91	174.45
4.30	0.95	137.45	0.51	149.28	0.013	86.12	0.91	173.35
4.40	0.95	133.74	0.49	145.93	0.015	77.51	0.91	172.11
4.50	0.95	129.79	0.48	140.55	0.017	73.28	0.91	170.84
4.60	0.95	124.99	0.48	136.95	0.020	66.34	0.90	169.42
4.70	0.95	120.07	0.48	131.34	0.021	58.68	0.90	168.05
4.80	0.95	113.93	0.48	126.35	0.024	52.95	0.90	166.61
4.90	0.95	106.51	0.50	120.05	0.027	44.93	0.89	165.05
5.00	0.95	97.54	0.50	113.46	0.031	37.57	0.89	163.57
5.10	0.95	86.55	0.53	105.86	0.036	28.40	0.88	161.77
5.20	0.95	73.45	0.55	96.22	0.041	19.22	0.87	160.12
5.30	0.95	56.67	0.57	85.88	0.047	7.98	0.86	158.23
5.40	0.94	37.29	0.60	71.99	0.053	-4.75	0.85	156.31
5.50	0.95	13.73	0.60	58.10	0.060	-19.80	0.83	154.40

MTTF Calculation
- Estimated MTTF -



Ea=1.6eV
Confidence Level=90%

Channel Temp. (deg.C)	MTTF (Hours)
160	4.05×10^7
180	6.07×10^6
200	1.07×10^6

$$AF = \exp[(-Ea/k)(1/T_{stress} - 1/T_{use})]$$

$$MTTF_{use} = MTTF_{stress} \times AF$$

Where;

AF : acceleration factor

Ea : activation energy (1.6eV)

k : Boltzmann's constant (8.62×10^{-5}eV/K)

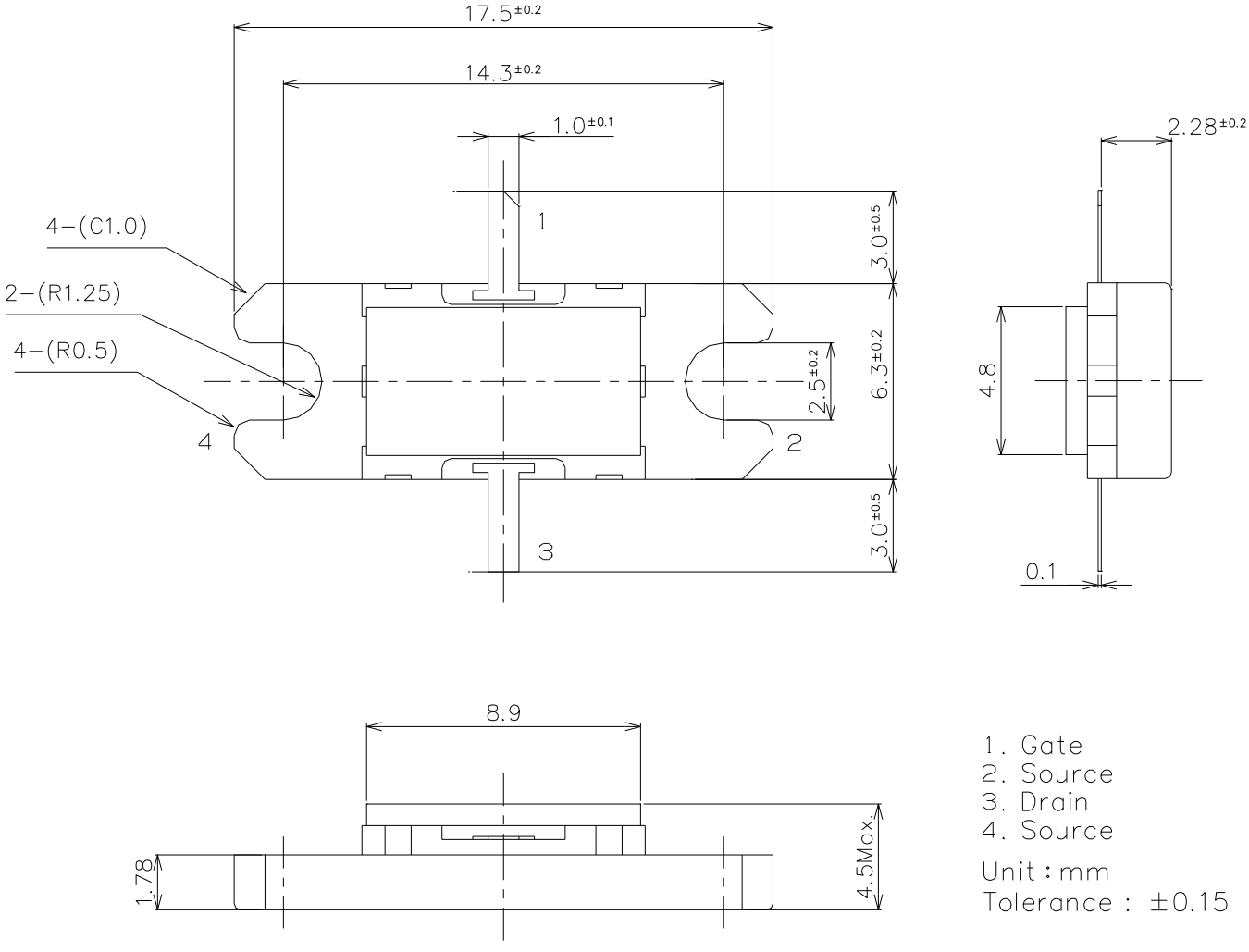
T_{stress} : stress temperature (K)

T_{use} : use temperature (K)

ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	0
Machine Model (per JEIA/ESD22-A115)	A

MK Package Outline
Metal-Ceramic Hermetic Package



For further information please contact:

http://global-sei.com/Electro-optic/about/office.html